CHANGE NOTIFICATION





Analog Devices, Inc. 1630 McCarthy Blvd., Milpitas CA (408) 432-1900

March 06, 2018

PCN_030618

Dear Sir/Madam:

Subject: Notification of Change to LTC4360-1, LTC4360-2 Datasheet

Please be advised that Analog Devices, Inc. Milpitas, California has made a minor change to the LTC4360-1, LTC4360-2 product datasheet to facilitate improvement in our manufacturing capability. The changes are shown on the attached page of the marked up datasheet. There was no change in form, fit, function, quality or reliability of the product. The product shipped after May 06, 2018 will be tested to the new limits.

Should you have any questions or concerns please contact your local Analog Devices sales representatives or you may contact me at 408-432-1900 ext. 2077, or by e-mail at <u>JASON.HU@ANALOG.COM</u>. If I do not hear from you by May 06, 2018, we will consider this change to be approved by your company.

Sincerely,

Jason Hu Quality Assurance Engineer

For questions on this PCN, please contact Jason Hu or you may send an email to your regional contacts below or contact your local ADI sales representatives.				
Americas: PCN_Americas@analog.com	Europe:	PCN_Europe@analog.com	Japan: Rest of Asia:	PCN_Japan@analog.com PCN_ROA@analog.com

new parameter

LTC4360-1/LTC4360-2

ELECTRICAL CHARACTERISTICS The • denotes the specifications which apply over the full operating temperature range, otherwise specifications are at $T_A = 25^{\circ}C$. $V_{IN} = 5V$, $V_{\overline{ON}} = 0V$ (LTC4360-1) unless otherwise noted. SYMBOL PARAMETER CONDITIONS MIN TYP MAX UNITS Supplies VIN Input Voltage Range • 2.5 80 V Input Undervoltage Lockout VIN Rising • 1.8 2.1 2.45 ۷ VIN(UVL) IIN Input Supply Current LTC4360-1 Von = 0V, LTC4360-2 • 220 400 μA LTC4360-1 Von = 2.5V • 1.5 10 μA Thresholds IN Pin Overvoltage Threshold 5.684 5.8 5.916 ۷ VIN(OV) VIN Rising • IN Pin Overvoltage Recovery Threshold V_{IN} Falling • 5.51 5.7 5.85 v VIN(OVL Overvoltage Hysteresis • 25 100 200 ΔV_{OV} m٧ **External Gate Drive** 300 ΔV_{GATE} External N-Channel MOSFET Gate Drive $\begin{array}{l} 2.5V \leq V_{IN} < 3V, \ I_{GATE} = -1 \mu A \\ 3V \leq V_{IN} < 5.5V, \ I_{GATE} = -1 \mu A \end{array}$ ٧ 4.5 6 ٠ 3.5 • v 4.5 7.9 6 (V_{GATE} – V_{OUT}) GATE High Threshold for PWRGD Status VGATE(TH) $V_{IN} = 3.3V$: 5.7 6.3 6.8 ۷ v V_{IN} = 5V 6.7 72 7.8 GATE Pull-Up Current V_{GATE} = 1V • -5 -10 -15 μA IGATE(UP) VGATE = 1V to 7V • 3 GATE Ramp-Up 1.5 4.5 V/ms VGATE(UP) GATE Fast Pull-Down Current Fast Turn-Off, VIN = 6V, VGATE = 9V • IGATE(FST) 15 30 60 mΑ GATE Pull-Down Current Von = 2.5V, VGATE = 9V (LTC4360-1) • 10 40 80 IGATE(DN) μA **Input Pins** IOUT(IN) OUT Input Current Vout = 5V, Von = 0V ٠ 5 10 20 μA Vout = 5V, Von = 2.5V • 0 ±3 μA VON(TH) ON Input Threshold (LTC4360-1) • 0.4 1.5 ۷ ON Pull-Down Current Von = 2.5V (LTC4360-1) • 2.5 5 10 μA ON Output Pins IN to GATEP Clamp Voltage VIN = 8V to 80V (LTC4360-2) 5 5.8 7.5 ٧ VGATEP(CLP) • GATEP Resistive Pull-down VGATEP = 3V (LTC4360-2) • 0.8 2 3.2 MΩ RGATEP PWRGD Output Low Voltage VIN = 5V, IPWRGD = 3mA • 0.23 0.4 ٧ VPWRGD(OL PWRGD Pull-Up Resistance to OUT VIN = 6.5V, VpWRGD = 1V • 250 500 800 kΩ RPWRGD Delay GATE On Delay ton VIN High to IGATE = -5µA ٠ 50 130 200 ms GATE Off Propagation Delay VIN = Step 5V to 6.5V to PWRGD High ٠ 0.25 toff 1 μs **t**PWRGD PWRGD Delay VIN = Step 5V to 6.5V • 0.25 1 US $V_{GATE} > \dot{V}_{GATE(TH)}$ to PWRGD Low 25 65 100 ms ON High to GATE Off Von = Step 0V to 2.5V (LTC4360-1) • 2 5 ton(OFF) μs

Note 1: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime. Note 3: An internal clamp limits V_{GATE} to a minimum of 4.5V above V_{OUT}. Driving this pin to voltages beyond this clamp may damage the device.

Note 2: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to GND unless otherwise specified.

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